

# 2SA720A

Silicon PNP epitaxial planer type

For low-frequency driver amplification

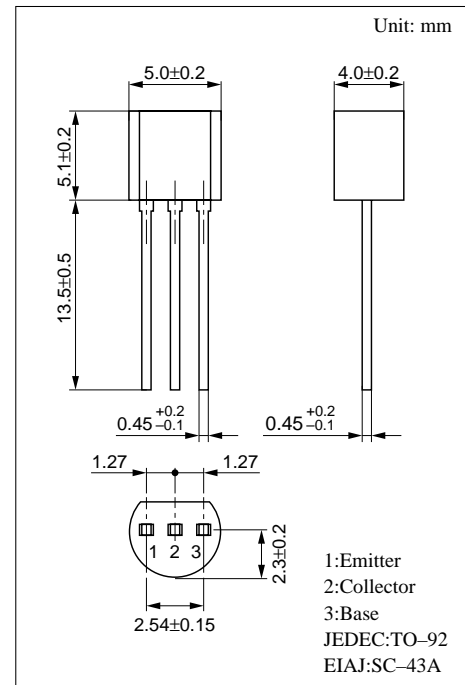
Complementary to 2SC1318A

## Features

- High collector to emitter voltage  $V_{CEO}$ .
- Optimum for the driver stage of a low-frequency and 25 to 30W output amplifier.

## Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	-80	V
Collector to emitter voltage	$V_{CEO}$	-70	V
Emitter to base voltage	$V_{EBO}$	-5	V
Peak collector current	$I_{CP}$	-1	A
Collector current	$I_C$	-0.5	A
Collector power dissipation	$P_C$	625	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 ~ +150	°C



## Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -20V, I_E = 0$			-0.1	$\mu A$
Collector to base voltage	$V_{CBO}$	$I_C = -10\mu A, I_E = 0$	-80			V
Collector to emitter voltage	$V_{CEO}$	$I_C = -2mA, I_B = 0$	-70			V
Emitter to base voltage	$V_{EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Forward current transfer ratio	$h_{FE1}^{*1}$	$V_{CE} = -10V, I_C = -150mA^{*2}$	85		240	
	$h_{FE2}$	$V_{CE} = -10V, I_C = -500mA^{*2}$	40			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -300mA, I_B = -30mA^{*2}$		-0.2	-0.6	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -300mA, I_B = -30mA^{*2}$		-0.85	-1.5	V
Transition frequency	$f_T$	$V_{CB} = -10V, I_E = 50mA, f = 100MHz$		120		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$		20	30	pF

\*2 Pulse measurement

\*1  $h_{FE1}$  Rank classification

Rank	Q	R
$h_{FE1}$	85 ~ 170	120 ~ 240

